SB2060LCT

DUAL LOW VF SCHOTTKY RECTIFIER

VOLTAGE 60 Volts **CURRENT** 20 Amperes

FEATURES

- Low forward voltage drop, low power losses
- High efficiency operation
- In compliance with EU RoHS 2002/95/EC directives

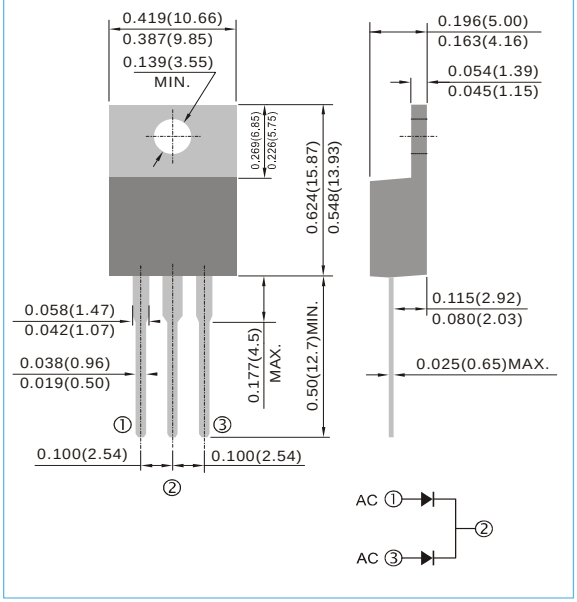
MECHANICAL DATA

Case : TO-220AB, Plastic

Terminals : Solderable per MIL-STD-750, Method 2026

Weight: 0.0655 ounces, 1.859 grams

TO-220AB Unit : inch(mm)



MAXIMUM RATINGS(T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	VALUE	UNIT
Maximum repetitive peak reverse voltage		V_{RRM}	60	V
Maximum average forward rectified current (Fig.4)	per device per diode	$I_{F(AV)}$	20 10	A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load per diode	per diode	I_{FSM}	145	A
Typical thermal resistance		$R_{\Theta JC}$	2.5	°C / W
Operating junction		T_J	-55 to + 125	°C
Storage temperature range		T_{STG}	-55 to + 150	°C

ELECTRICAL CHARACTERISTICS(T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Breakdown voltage	V_{BR}	I_R=1mA		64	68	-	V
Instantaneous forward voltage per diode (1)	V_F	I_F=5A I_F=10A	T_J=25°C	- -	0.44 0.51	0.51 0.60	V
		I_F=5A I_F=10A	T_J=125°C	- -	- -	0.44 0.56	V
Reverse current per diode (2)	I_R	V_R=60V	T_J=25°C T_J=100°C	- -	- -	0.5 20	mA

Note.1.Pulse test : 380μs pulse width, 1% duty cycle

2.Pulse test : Pulse width ≤ 2.5ms

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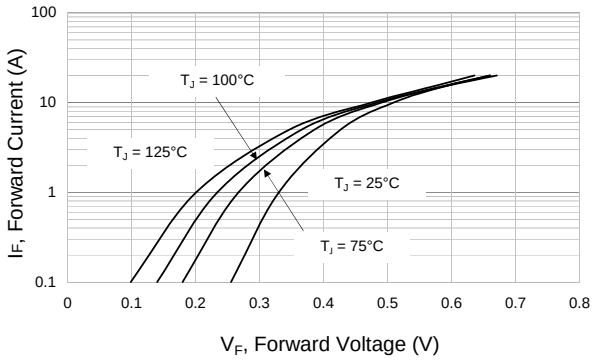

Fig.1 Typical Forward Characteristics Per Diode

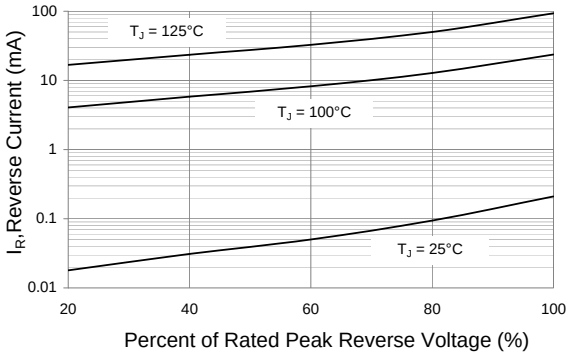

Fig.2 Typical Reverse Characteristics Per Diode

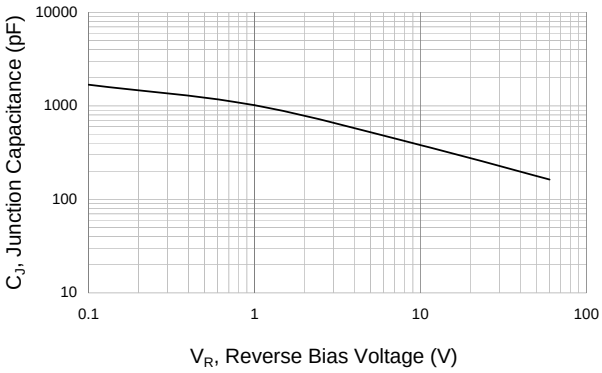

Fig.3 Typical Junction Capacitance Per Diode

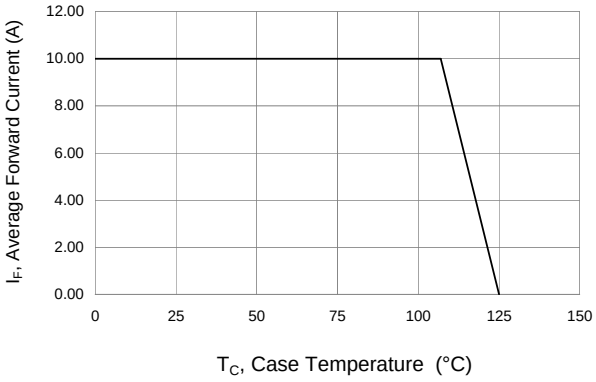

Fig.4 Forward Current Derating Curve Per Diode